## Quad 2-Input NOR Gate <br> High-Performance Silicon-Gate CMOS

The 74 HCO 2 is identical in pinout to the LS 02 . The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

## Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: $1.0 \mu \mathrm{~A}$
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 40 FETs or 10 Equivalent Gates
- These are Pb -Free Devices



$$
\begin{array}{ll}
\mathrm{HCO} 2 & =\text { Device Code } \\
\mathrm{A} & =\text { Assembly Location } \\
\text { WL or L } & =\text { Wafer Lot } \\
\mathrm{Y} & =\text { Year } \\
\text { WW or W Work Week } \\
\text { G or } \quad & =\text { Pb-Free Package }
\end{array}
$$

(Note: Microdot may be in either location)

FUNCTION TABLE

| Inputs |  | Output |
| :---: | :---: | :---: |
| A | B | Y |
| L | L | H |
| L | H | L |
| H | L | L |
| H | H | L |

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.
(8)

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage (Referenced to GND) | -0.5 to +7.0 | V |
| $\mathrm{~V}_{\text {in }}$ | DC Input Voltage (Referenced to GND) | -0.5 to $\mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| $\mathrm{~V}_{\text {out }}$ | DC Output Voltage (Referenced to GND) | -0.5 to $\mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| $\mathrm{I}_{\text {in }}$ | DC Input Current, per Pin | $\pm 20$ | mA |
| $\mathrm{I}_{\text {out }}$ | DC Output Current, per Pin | $\pm 25$ | mA |
| $\mathrm{I}_{\mathrm{CC}}$ | DC Supply Current, $\mathrm{V}_{\mathrm{CC}}$ and GND Pins | $\pm 50$ | mA |
| $\mathrm{P}_{\mathrm{D}}$ | Power Dissipation in Still Air,SOIC Package $\dagger$ <br> TSSOP Package $\dagger$ | 500 | mW |
| $\mathrm{~T}_{\text {stg }}$ | Storage Temperature | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{L}}$ | Lead Temperature, 1 mm from Case for 10 Seconds |  |  |
| SOIC or TSSOP Package |  |  |  |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, $\mathrm{V}_{\text {in }}$ and $V_{\text {out }}$ should be constrained to the range GND $\leq\left(\mathrm{V}_{\text {in }}\right.$ or $\left.\mathrm{V}_{\text {out }}\right) \leq \mathrm{V}_{\mathrm{CC}}$.
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $\mathrm{V}_{\mathrm{CC}}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
$\dagger$ Derating - SOIC Package: $-7 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $65^{\circ}$ to $125^{\circ} \mathrm{C}$
TSSOP Package: $-6.1 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ from $65^{\circ}$ to $125^{\circ} \mathrm{C}$
For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage (Referenced to GND) | 2.0 | 6.0 | V |
| $\mathrm{~V}_{\text {in }}, \mathrm{V}_{\text {out }}$ | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | $\mathrm{~V}_{\mathrm{CC}}$ | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature, All Package Types | -55 | +125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise and Fall Time | (Figure 1) | $\mathrm{V}_{\mathrm{CC}}=2.0 \mathrm{~V}$ | 0 |
|  |  | $\mathrm{~V}_{\mathrm{CC}}=4.5 \mathrm{~V}$ | 0 | 5000 |
|  |  | nss |  |  |
|  |  | $\mathrm{V}_{\mathrm{CC}}=6.0 \mathrm{~V}$ | 0 | 400 |
|  |  |  |  |  |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| Symbol | Parameter | Test Conditions | $\mathrm{V}_{\mathrm{cc}}$ <br> (V) | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $\begin{gathered} -55 \text { to } \\ 25^{\circ} \mathrm{C} \end{gathered}$ | $\leq 85^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Minimum High-Level Input Voltage | $\begin{aligned} & \hline \mathrm{V}_{\text {out }}=0.1 \mathrm{~V} \text { or } \mathrm{V}_{\mathrm{CC}}-0.1 \mathrm{~V} \\ & \left.\right\|_{\text {lout }} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \hline 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{gathered} \hline 1.5 \\ 2.1 \\ 3.15 \\ 4.2 \end{gathered}$ | $\begin{gathered} 1.5 \\ 2.1 \\ 3.15 \\ 4.2 \end{gathered}$ | $\begin{gathered} 1.5 \\ 2.1 \\ 3.15 \\ 4.2 \end{gathered}$ | V |
| $\mathrm{V}_{\text {IL }}$ | Maximum Low-Level Input Voltage | $\begin{aligned} & \mathrm{V}_{\text {out }}=0.1 \mathrm{~V} \text { or } \mathrm{V}_{\mathrm{CC}}-0.1 \mathrm{~V} \\ & \mathrm{l}_{\text {out }} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{gathered} \hline 0.5 \\ 0.9 \\ 1.35 \\ 1.8 \end{gathered}$ | $\begin{gathered} \hline 0.5 \\ 0.9 \\ 1.35 \\ 1.8 \end{gathered}$ | $\begin{gathered} \hline 0.5 \\ 0.9 \\ 1.35 \\ 1.8 \end{gathered}$ | V |
| $\mathrm{V}_{\mathrm{OH}}$ | Minimum High-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ & \mid \\|_{\text {outt }} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \hline 2.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & \hline 1.9 \\ & 4.4 \\ & 5.9 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 4.4 \\ & 5.9 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 4.4 \\ & 5.9 \end{aligned}$ | V |
|  |  | $\mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IH}}$ or $\mathrm{V}_{\mathrm{IL}}$ $\left\|\\|_{\text {out }}\right\| \leq 2.4 \mathrm{~mA}$ <br>  <br>  <br> $\left\|\left.\right\|_{\text {out }}\right\| \leq 4.0 \mathrm{~mA}$ <br> $\mid \mathrm{l}_{\text {out }}$$\leq 5.2 \mathrm{~mA}$ | $\begin{aligned} & \hline 3.0 \\ & 4.5 \\ & 6.0 \\ & \hline \end{aligned}$ | $\begin{aligned} & \hline 2.48 \\ & 3.98 \\ & 5.48 \\ & \hline \end{aligned}$ | $\begin{aligned} & 2.34 \\ & 3.84 \\ & 5.34 \\ & \hline \end{aligned}$ | $\begin{gathered} 2.20 \\ 3.7 \\ 5.2 \\ \hline \end{gathered}$ |  |
| $\mathrm{V}_{\text {OL }}$ | Maximum Low-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\text {IH }} \text { or } \mathrm{V}_{\text {IL }} \\ & \\|_{l_{\text {out }}} \leq 20 \end{aligned}$ | $\begin{aligned} & 2.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & \hline 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & \hline 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & \hline 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | V |
|  |  | $\begin{array}{\|ll} \hline \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} & \begin{array}{l} \mid \\|_{\text {out }} \leq 2.4 \mathrm{~mA} \\ \\ \\ \\ \\ \left\|\left.\right\|_{\text {out }}\right\| \leq 4.0 \mathrm{~mA} \\ \left\|l_{\text {out }}\right\| \leq 5.2 \mathrm{~mA} \end{array} \\ \hline \end{array}$ | $\begin{aligned} & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 0.26 \\ & 0.26 \\ & 0.26 \end{aligned}$ | $\begin{aligned} & 0.33 \\ & 0.33 \\ & 0.33 \end{aligned}$ | $\begin{aligned} & \hline 0.4 \\ & 0.4 \\ & 0.4 \end{aligned}$ |  |
| $\mathrm{lin}_{\text {in }}$ | Maximum Input Leakage Current | $\mathrm{V}_{\text {in }}=\mathrm{V}_{\text {cc }}$ or GND | 6.0 | $\pm 0.1$ | $\pm 1.0$ | $\pm 1.0$ | $\mu \mathrm{A}$ |
| $I_{\text {cc }}$ | Maximum Quiescent Supply Current (per Package) | $\begin{aligned} & \hline \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{CC}} \text { or GND } \\ & \left.\right\|_{\text {lout }}=0 \mu \mathrm{~A} \end{aligned}$ | 6.0 | 2.0 | 20 | 40 | $\mu \mathrm{A}$ |

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ( $\mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$, $\left.\operatorname{Input} \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=6.0 \mathrm{~ns}\right)$

| Symbol | Parameter | $\mathrm{V}_{\mathrm{cc}}$ <br> (V) | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | $\begin{gathered} -55 \text { to } \\ 25^{\circ} \mathrm{C} \end{gathered}$ | $\leq 85^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\begin{aligned} & \text { tpLH, } \\ & \mathrm{t}_{\text {PHL }} \end{aligned}$ | Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2) | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 75 \\ & 30 \\ & 15 \\ & 13 \end{aligned}$ | $\begin{aligned} & 95 \\ & 40 \\ & 19 \\ & 16 \end{aligned}$ | $\begin{aligned} & 110 \\ & 55 \\ & 22 \\ & 19 \end{aligned}$ | ns |
| $\begin{aligned} & \mathrm{t}_{\mathrm{TLH}}, \\ & \mathrm{t}_{\mathrm{THL}} \end{aligned}$ | Maximum Output Transition Time, Any Output (Figures 1 and 2) | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 75 \\ & 30 \\ & 15 \\ & 13 \end{aligned}$ | $\begin{aligned} & 95 \\ & 40 \\ & 19 \\ & 16 \end{aligned}$ | $\begin{aligned} & 110 \\ & 55 \\ & 22 \\ & 19 \end{aligned}$ | ns |
| $\mathrm{C}_{\text {in }}$ | Maximum Input Capacitance | - | 10 | 10 | 10 | pF |

NOTE: For propagation delays with loads other than 50 pF , and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

| $\mathrm{C}_{\text {PD }}$ |  | Typical @ $25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{cc}}=5.0 \mathrm{~V}$ | pF |
| :---: | :---: | :---: | :---: |
|  | Power Dissipation Capacitance (Per Gate)* | 22 |  |

*Used to determine the no-load dynamic power consumption: $P_{D}=C_{P D} V_{C C}{ }^{2}+I_{C C} V_{C C}$. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
${ }^{\circ}$


Figure 1. Switching Waveforms

*Includes all probe and jig capacitance
Figure 2. Test Circuit


Figure 3. Expanded Logic Diagram
(1/4 of the Device)

## X-ON Electronics

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